安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO. , LTD.

SS32-SS310

SMB Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降
High current capability 高电流能力
Surface mount device 表面贴装器件
Case 封装:SMB(DO-214AA)

■Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	SS32	SS33	SS34	SS35	SS36	SS38	SS39	SS310	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	30	40	50	60	80	90	100	V
DC Reverse Voltage 直流反向电压	V_R	20	30	40	50	60	80	90	100	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	14	21	28	35	42	56	63	70	V
Forward Rectified Current 正向整流电流	I_F	3								A
Peak Surge Current 峰值浪涌电流	I_{FSM}	80								A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	10								℃/W
Junction Temperature 结温	T_J	150								℃
Storage Temperature 储藏温度	T_{stg}	-65to+150℃								℃

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	SS32-SS34	SS35-SS36	SS38-SS310	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.55	0.70	0.80	V	I_F=3A
Reverse Current 反向电流	I_R(25℃) (100℃)	0.1 5		0.02 2	mA	V_R=V_{RRM}
Diode Capacitance 二极管电容	C_D	300			pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

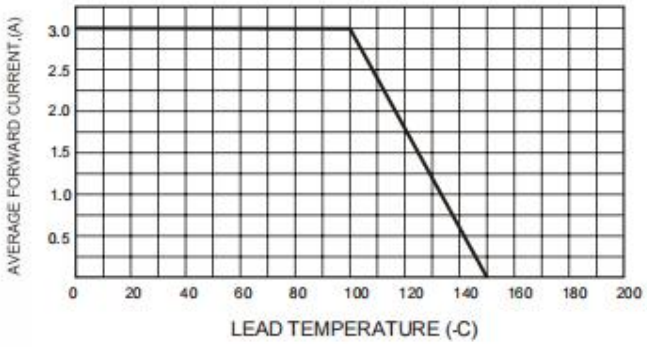


FIG.2-TYPICAL FORWARD CHARACTERISTICS

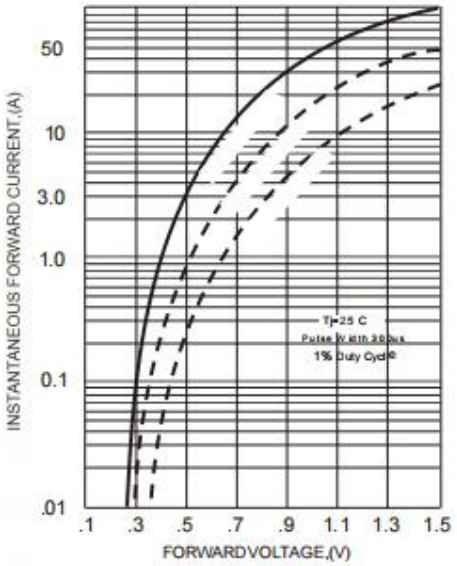


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

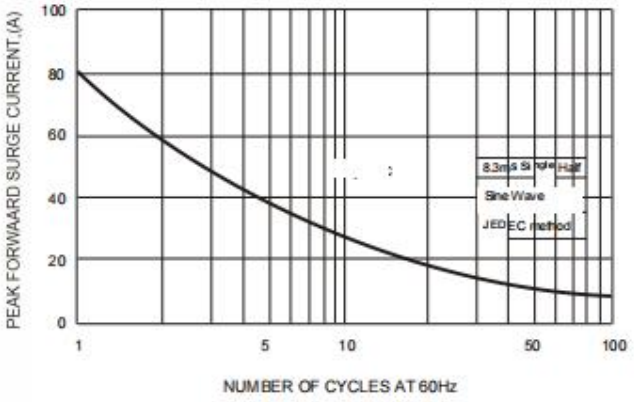


FIG.4-TYPICAL JUNCTION CAPACITANCE

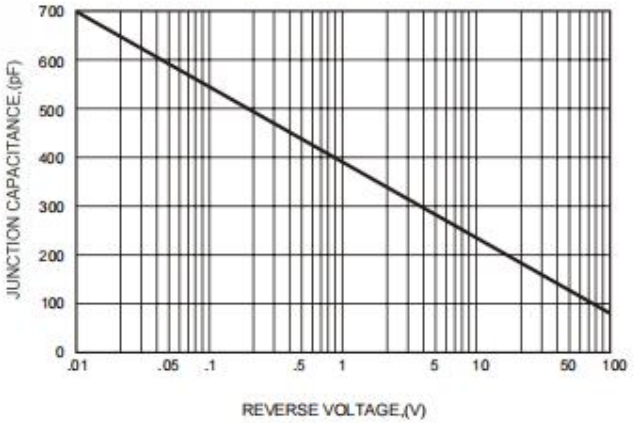
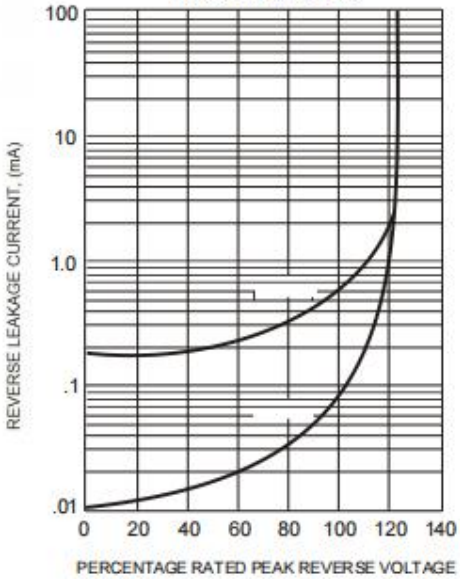
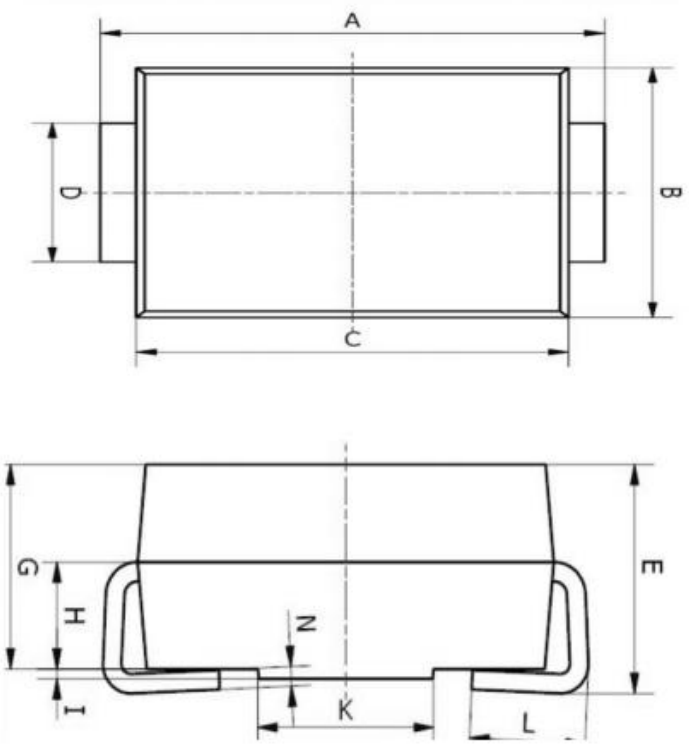


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



■**Dimension** 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	5.00	5.45	0.197	0.215
B	3.20	4.00	0.126	0.157
C	4.30	4.70	0.169	0.185
D	1.80	2.20	0.071	0.087
E	2.20	2.50	0.087	0.098
G	1.90	2.30	0.075	0.090
H	0.95	1.25	0.037	0.049
I	0.05	0.15	0.002	0.006
K	1.70	2.10	0.067	0.083
L	0.90	1.60	0.035	0.063
N	0.10	0.30	0.004	0.012